

L Number	Hits	Search Text	DB	Time stamp
1	287	438/276.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:05
2	636	438/199.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:06
3	116	438/223.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:06
4	150	438/224.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:06
5	634	438/227.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:06
6	270	438/228.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:07
7	209	438/153.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:08
8	762	438/154.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:09
-	2	6258673.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:03
-	2	5866445.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 14:23
-	2	20020019099.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:00
-	14	double adj cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:37
-	80	multiple adj cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:36
-	2	multi adj cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:37

-	661	plurality adj cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:38
-	193	(plurality adj cmos) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:18
-	43	plural adj cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:17
-	77	(plurality adj cmos) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:19
-	335	cmos adj pair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:39
-	6	multiple adj (complementary adj metal adj oxide adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:37
-	0	double adj (complementary adj metal adj oxide adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:37
-	0	multi adj (complementary adj metal adj oxide adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:38
-	40	plurality adj (complementary adj metal adj oxide adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:39
-	0	plural adj (complementary adj metal adj oxide adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:39
-	5	(complementary adj metal adj oxide adj semiconductor) adj pair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:40
-	219	different adj gate adj oxide adj thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 15:58
-	119	gate adj oxide adj thicker	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 16:00
-	132	gate adj oxide adj thinner	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 16:00